100V N-Channel Power SpeedFET

● General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It is suitable for automotive application.

● Features

■AEC-Q101 Qualified

■Low $R_{DS(ON)}$ to minimize conductive loss

■Low Gate Charge for fast switching

■Low Thermal resistance

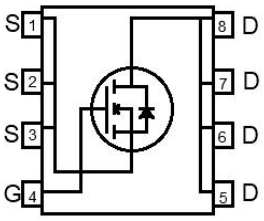
●Application

■BLDC Motor driver

■DC-DC

■Load Switch

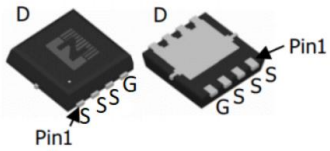
● Product Summary



V_{DS}= 100V

$R_{DS(ON)}$ = 50mΩ

I_D= 14A



DFN3*3

RoHS

REACH COMPLIANT

HF

●Ordering Information:

Part NO.	ZMSA420N10M
Marking	420N10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

●Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		100	V
Gate-Source Voltage①	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25℃	14	A
	I_D	T_C=75℃	11	A
	I_D	T_C=100℃	10	A
Pulsed Drain Current	I_{DM}	Pulsed; t_p ≤ 10 μs; T_{mb} = 25 °C;	56	A
Total Power Dissipation	P_D	T_C=25℃	27	W
Total Power Dissipation	P_D	T_A=25℃	2.5	W
Operating Junction Temperature	T_J		-55 to +175	℃
Storage Temperature	T_{STG}		-55 to +175	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=10V, Rg=25Ω,	10	mJ
		L=0.5mH, V_{GS}=10V, Rg=25Ω,	21	mJ
ESD Level (HBM)	CLASS 1B			

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	5.6	°C/W
Thermal resistance, junction-ambient②	R_{thJA}		-	60	°C/W
Soldering temperature (total time<10s)	Tsold		-	260	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250uA	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	1.3	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= 100V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} = 0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D= 10A		50	65	mΩ
		V_{GS}=4.5V, I_D= 6A		64	83	mΩ
Forward Transconductance	g_{FS}	V_{DS} =5V, I_{SD} = 10A		4		s
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = 10A			1.3	V

●Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=25V	-	275	-	pF
Output capacitance	Coss		-	146	-	
Reverse transfer capacitance	Crss		-	3.7	-	
Gate Risistance	Rg	f = 1MHz	-	1.3		Ω
Total gate charge	Qg	V_{DD} = 15V, I_D = 20A, V_{GS} = 10V	-	7	-	nC
	Qg (4.5v)		-	4	-	
Gate - Source charge	Qgs		-	2.1	-	
Gate - Drain charge	Qgd		-	1.1	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=15V, R_G =3.3Ω, I_D =20A	-	10	-	ns
Turn-ON Rise time	t_r		-	4.2	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	15	-	ns
Turn-Off Fall time	t_f		-	4.4	-	ns
Reverse Recovery Time	t_{RR}	V_{DD}=20V, dI_S/dt = 100A/us, I_S=20A	-	57	-	ns
Reverse Recovery Charge	Q_{RR}		-	80	-	nC

Fig.1 Gate-Charge Characteristics

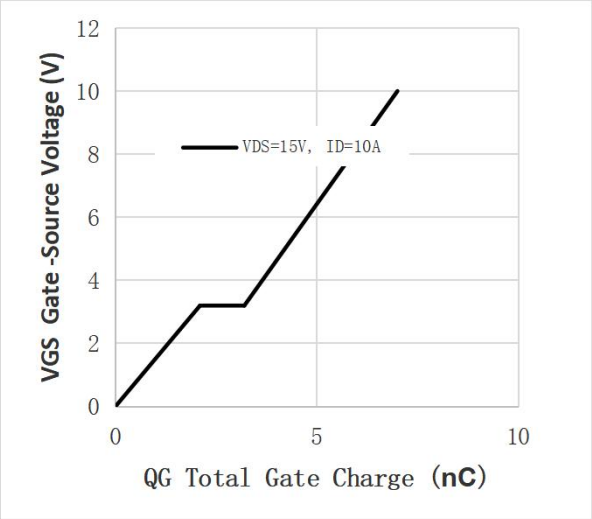


Fig.2 Capacitance Characteristics

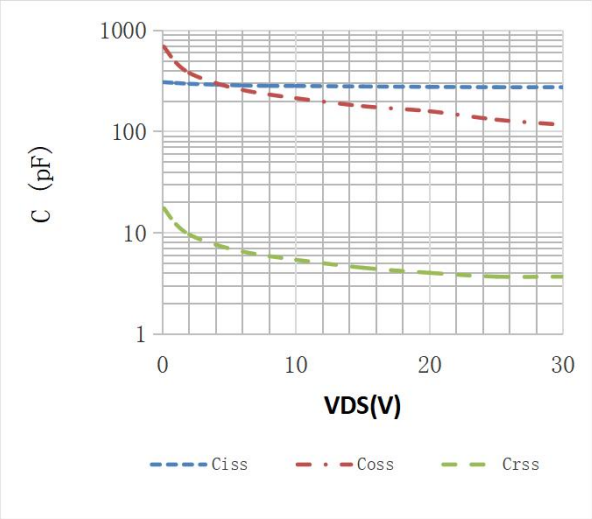


Fig.3 Power Dissipation

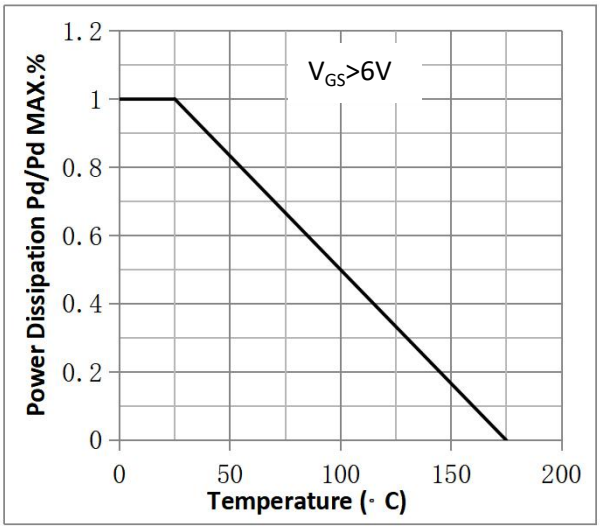


Fig.4 Typical output Characteristics

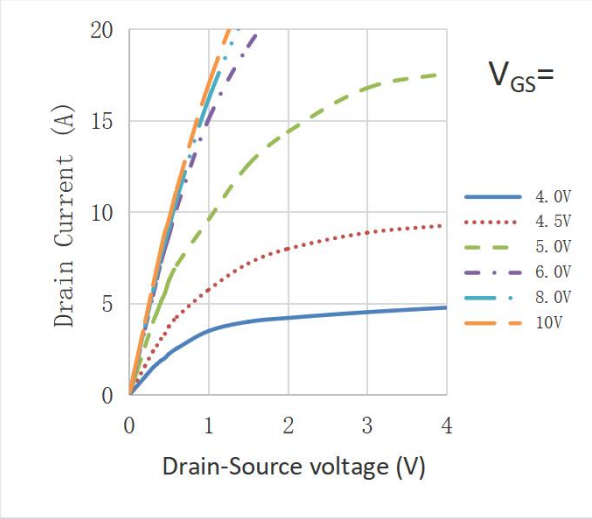


Fig.5 Threshold Voltage V.S Junction Temperature

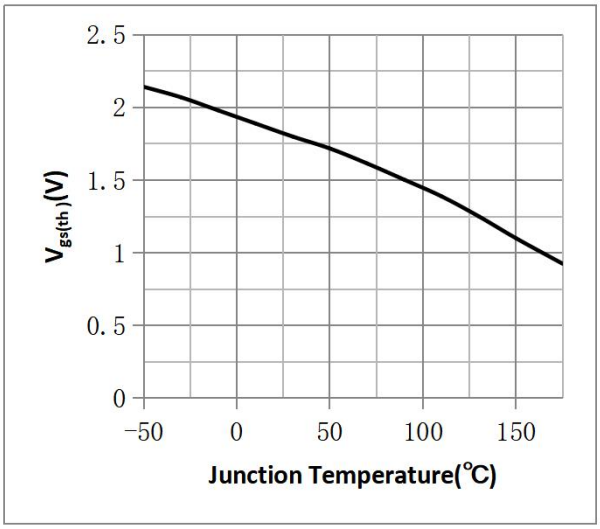


Fig.6 Resistance V.S Drain Current

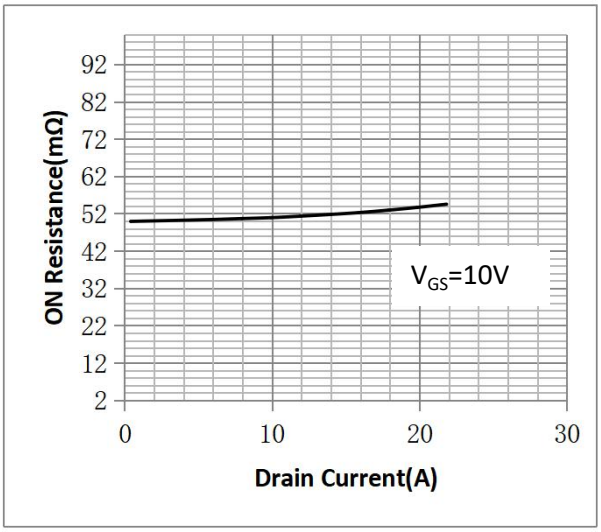


Fig.7 On-Resistance VS Gate Source Voltage

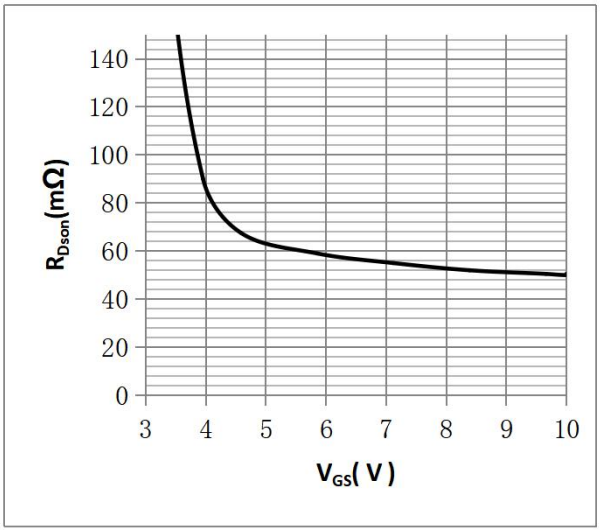


Fig.8 On-Resistance V.S Junction Temperature

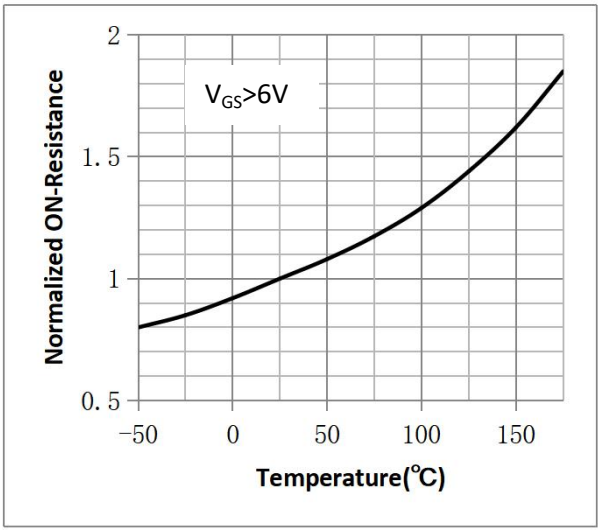


Figure 9. Diode Forward Voltage vs. Current

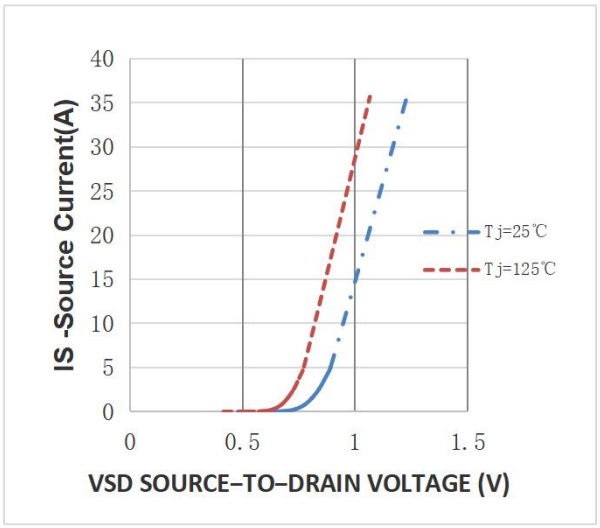


Figure 10. Transfer Characteristics

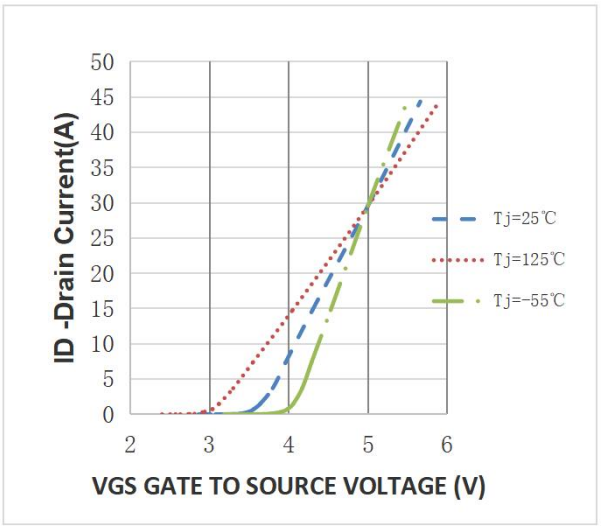


Fig.11 Safe Operating Area

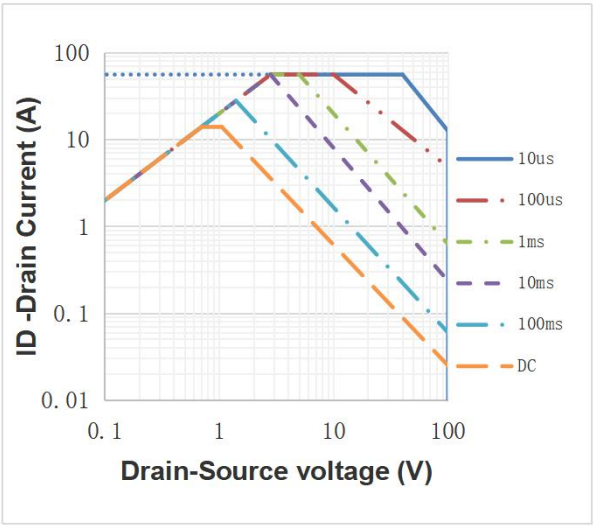
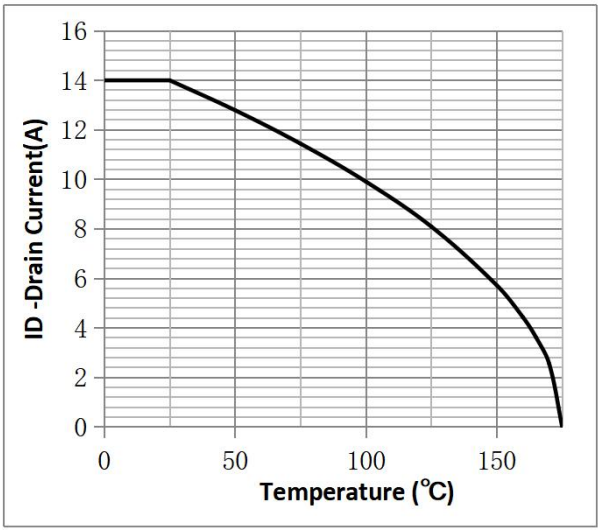
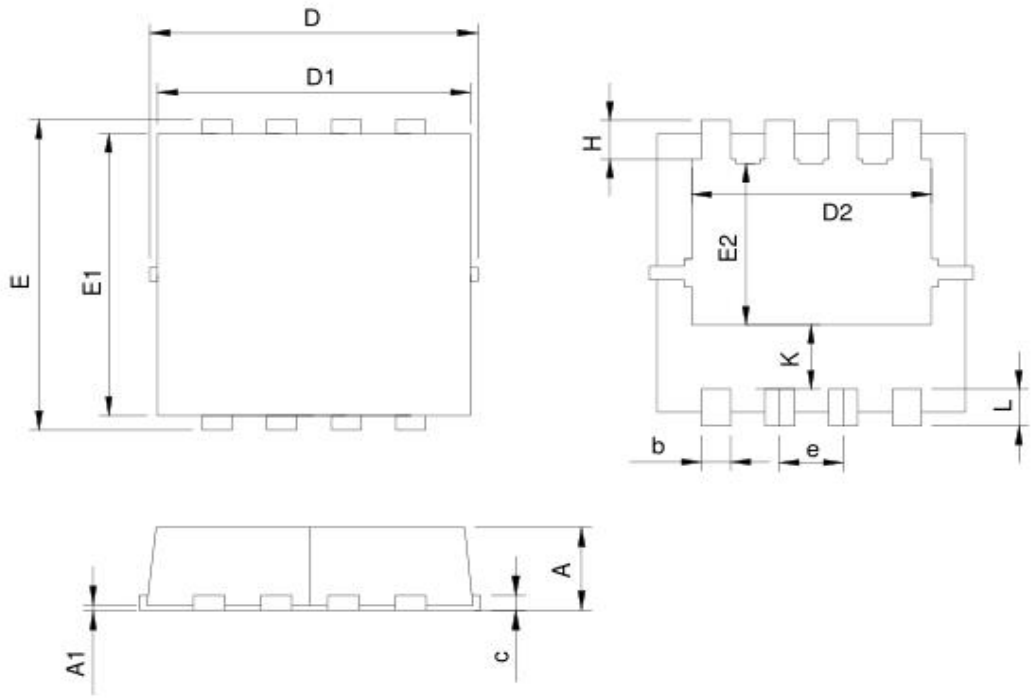


Fig.12 ID vs. Case Temperature③

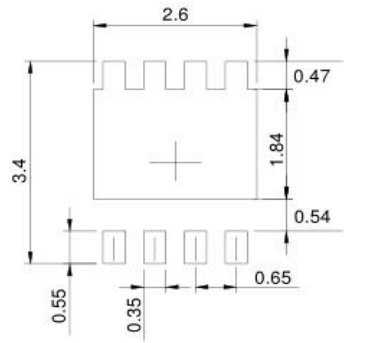


●DFN3*3 Package Outline



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm

Note:

① Pulse : VGS=+20V/-20V, Duty cycle=50%,Tj=175℃, t=1000 hours; For DC， the following test conditions can be passed: VGS=+20V/-10V, Tj=175℃, t=1000 hours；

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

③Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

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Revision History

Version	Date	Change
A	2021.12.10	
B	2022.10.20	1.Add Reach,HF figure,2.Fig1~12 modify 3.Add It is suitable for automotive application.4.Add Dynamic characteristics